

DATASHEET

Modulo TVDE	DDR2 4GB/2GB/1GB/512MB			
Module TYPE	SODIMM			
Module speed	PC-6400			
CAS Latency	CL-6			
Pin	200pin			
SDRAM Operating Temp	-40 ℃ ~85 ℃			

Total Solution For Industrial DRAM Module



1. Features

Key Parameter

Industry	Speed	Data Rate MT/s		tRCD	tRP	tRC	
Nomenclature	Grade	CL=4	CL=5	CL=6	(ns)	(ns)	(ns)
PC2-6400	-	533	667	800	15	15	60

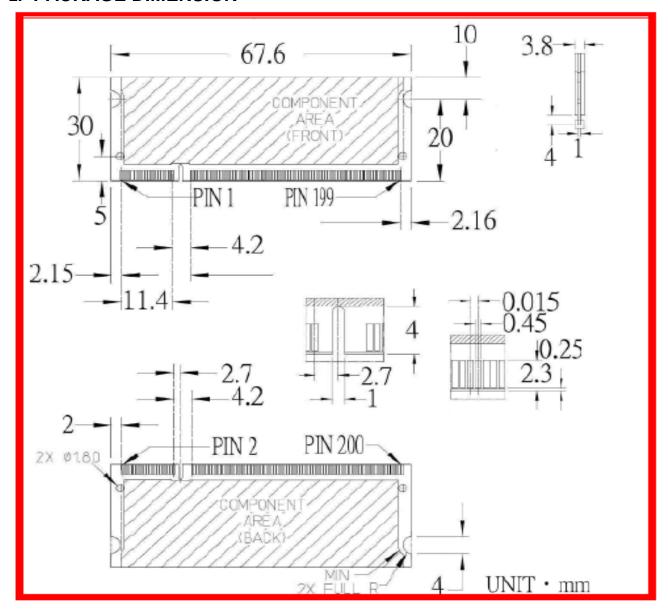
- JEDEC Standard 200-pin Dual In-Line Memory Module
- Intend for 400MHz applications
- Inputs and Outputs are SSTL-18 compatible
- VDD=VDDQ= 1.8 Volt \pm 0.1
- Differential clock input
- All inputs are sampled at the positive going edge of the system clock
- Bi-Directional data strobe with one clock cycle preamble and one-half clock post-amble
- Address and control signals are fully synchronous to positive clock edge.
- Auto Refresh (CBR) and Self Refresh Modes support.
- Serial Presence Detect with EEPROM

- Automatic and controlled precharge commands.
- Auto & self refresh 7.8 μ s (TA \leq +85°C)
- •30u"Golden Contactor
- SDRAM Operation Temperature (Note 1)
 - $-40^{\circ}C \le TA \le +85^{\circ}C$
- Programmable Device Operation:
 - Burst Type: Sequential or Inteleave
 - Operation: Burst Read and Write
 - Device CAS# Latency: 6
 - Burst Length: 4, 8
- RoHS Compliant (Section 15)

Note: 1. The refresh rate is required to double when Tc exceeds 85°C.



2. PACKAGE DIMENSION



Note: Device position is only for reference.